



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-89 Plastic-Encapsulate Transistors

KTD1898 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 500 mW ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 1 A

Collector-base voltage

$V_{(BR)CBO}$: 100 V

Operating and storage junction temperature range

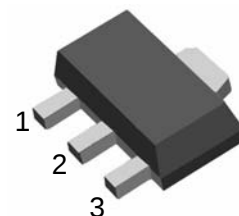
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	100			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=80V, I_E=0$			1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$			1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=3V, I_C=500mA$	70		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=20mA$			0.4	V
Transition frequency	f_T	$V_{CE}=10V, I_C=50mA$		100		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		20		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y	GR
Range	70-140	120-240	200-400
Marking	ZO	ZY	ZG